

Amendments to the Claims:

The following claims will replace all prior versions of the claims in this application (in the unlikely event that no claims follow herein, the previously pending claims will remain):

1. (Currently Amended) A method of forming a metal line layer in a semiconductor device, comprising:
depositing a ~~first, second and third conductive layers~~ diffusion barrier layer, a metal layer and an anti reflection layer on a semiconductor substrate;
depositing an insulating film on the ~~third conductive~~ anti reflection layer;
depositing and patterning a photosensitive material on the insulating film;
etching portions of the insulating film, the ~~third and second conductive layers~~ anti reflection layer and the metal layer using activated plasma and the photosensitive material as a mask, whereby portions of side walls of the metal layer are over-etched by plasma ions;
removing the photosensitive material;
forming a side wall oxide film on the over-etched side walls of the ~~second conductive~~ metal layer by reacting the ~~second conductive~~ metal layer with ozone; and
etching portions of the ~~first conductive~~ diffusion barrier layer using the insulating film as a ~~hard~~ etch mask.
2. (Currently Amended) A method of forming a metal line layer in a semiconductor device according to claim 1, wherein the ~~second conductive~~ metal layer is made of aluminum (Al).
3. (Currently Amended) A method of forming a metal line layer in a semiconductor device according to claim 1, wherein the ~~metal line~~ diffusion barrier layer is ~~formed by laminating a first~~ made of Ti/TiN layer, ~~an Al layer and the anti reflection layer is made of a second~~ Ti/TiN layer ~~in this order~~, and the side wall oxide film is an Al₂O₃ film.
4. (Currently Amended) A method of forming a metal line in a semiconductor memory device according to claim 1, wherein the ~~third, second and first conductive layers~~ the anti reflection layer, the metal layer and the diffusion barrier layer are dry-etched using activated plasma comprising Cl₂/BCl₃/N₂ gas.

5. (Canceled)
6. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 1, wherein the insulating film is a nitride film.
7. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 1, wherein the insulating film is etched by means of a dry etching process using activated plasma comprising a combination of $\text{CHF}_3/\text{CF}_4/\text{Ar}$ or C_xF_y (where x, y are natural numbers)/ O_2/Ar gas.
8. (Canceled)
9. (Currently Amended) A method of forming a metal line layer in a semiconductor device, comprising:
 - depositing a first, second and third conductive layers on a semiconductor substrate;
 - depositing an insulating film on the third conductive layer;
 - dry etching portions of the insulating film, the third and the second conductive layers using activated plasma, whereby a portions of side walls of the second conductive layer are over-etched by plasma ions;
 - forming a side wall oxide film on the side walls of the over-etched second conductive layer by reacting the second conductive layer with ozone; and
 - etching portions of the first conductive layer using the insulating film as a ~~hard~~ an etch mask.
10. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 9, wherein the first conductive layer is made of Ti/TiN layer, the second conductive layer is made of aluminum (Al), and the third conductive layer is made of Ti/TiN layer.
11. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 9, wherein the side wall oxide film is an Al_2O_3 film.
12. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 9, wherein the insulating film is a nitride film.

13. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 9, wherein the insulating film is etched by means of a dry etching process using activated plasma comprising a combination of $\text{CHF}_3/\text{CF}_4/\text{Ar}$ or C_xF_y (where x, y are natural numbers)/ O_2/Ar gas.

14. (Previously Presented) A method of forming a metal line in a semiconductor memory device according to claim 9, wherein the third and second conductive layers are dry-etched using activated plasma comprising $\text{Cl}_2/\text{BCl}_3/\text{N}_2$ gas.